

IN THE SPECIFICATION

Please amend a portion of the specification on lines 13-17 on page 14 as follows:

As illustrated by the cross-hatched diagram in Fig. 4, showing part of the beam cross-sectional areas 45 of the diode lasers 43, for laser treatment of a semiconductor wafer [[40]] 14 having a reduced diameter in comparison with the semiconductor wafer 12, only a part of the diode laser 43 according to a partial matrix 53 needs be activated.